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<p>Application Number</p>		<p>New Application</p>			
<p>Filing Date</p>		<p>December 16, 2003</p>			
<p>First Named Inventor</p>		<p>Etsuko ASANO et al.</p>			
<p>Art Unit</p>					
<p>Examiner</p>					
Sheet	1	of	1	<p>Attorney Docket Number</p>	
				<p>740756-2688</p>	

FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Application of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>2</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> (If known)				
REB	JP 08-139044		05/31/1996	Otani		Abstract

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
PEP		Mitsumasa KOYANAGI, "SUBMICRON DEVICE II", Maruzen Kabushiki Kaisha Shuppan, 1987, pp. 121-142.	
PEP		Masahide INUISHI et al., "A HIGH PERFORMANCE AND HIGHLY RELIABLE DUAL GATE CMOS WITH GATE/N OVERLAPPED LDD APPLICABLE TO THE CRYOGENIC OPERATION", IEDM, 1989, pp. 773-776.	
PEP		Takashi HORI, "1/4- $\mu$ m LATID (LArge-Tilt-angle Implanted Drain) TECHNOLOGY FOR 3.3-V OPERATION", IEDM 1989, pp. 777-780.	

Examiner Signature		Date Considered	1/20/06
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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